

# SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

# TIG064E8 - N-Channel IGBT

# N-Channel IGBT Light-Controlling Flash Applications

· Built-in Gate-to-Emitter protection diode

• Low voltage drive (2.5V)

dv / dt guarantee\*

# Features

- · Low-saturation voltage
- Enhansment type
- Mounting Height 0.9mm, Mounting Area 8.12mm<sup>2</sup>
- Halogen free compliance

# **Specifications**

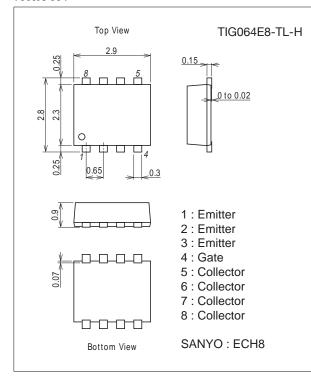
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Emitter Voltage	VCES		400	V
Gate-to-Emitter Voltage (DC)	VGES		±4	V
Gate-to-Emitter Voltage (Pulse)	VGES	PW≤1ms	±5	V
Collector Current (Pulse)	ICP	V <sub>GE</sub> =2.5V, C <sub>M</sub> =100µF	150	А
Maximum Collector-to-Emitter dv / dt	dV <sub>CE</sub> / dt	V <sub>CE</sub> ≤320V, starting Tch=25°C	400	V/μs
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-40 to +150	°C

\* : Concerning dv / dt (slope of Collector Voltage at the time of Turn-OFF), dv / dt > 400V /  $\mu$ s will be 100% screen-detected in the circuit shown as Fig. 1.

#### Package Dimensions

unit : mm (typ) 7011A-004

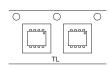


#### Product & Package Information

- Package : ECH8
- JEITA, JEDEC
- Minimum Packing Quantity : 3000 pcs./reel

: -

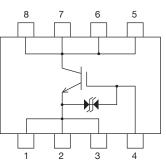
#### Packing Type: TL





Marking

#### **Electrical Connection**

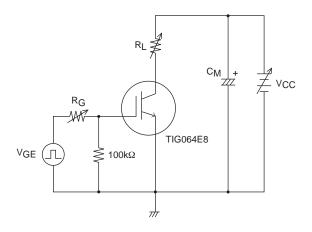


SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

Parameter	Cumphel	Conditions	Ratings			Linit
	Symbol	Conditions	min	typ	max	Unit
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I <sub>C</sub> =2mA, V <sub>GE</sub> =0V	400			V
Collector-to-Emitter Cutoff Current	ICES	V <sub>CE</sub> =320V, V <sub>GE</sub> =0V			10	μΑ
Gate-to-Emitter Leakage Current	IGES	V <sub>GE</sub> =±4V, V <sub>CE</sub> =0V			±10	μA
Gate-to-Emitter Threshold Voltage	V <sub>GE</sub> (off)	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	0.4		0.9	V
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	IC=100A, VGE=2.5V		4.2	7	V
Input Capacitance	Cies			3100		pF
Output Capacitance	Coes	V <sub>CE</sub> =10V, f=1MHz		30		pF
Reverse Transfer Capacitance	Cres			23		pF

#### Electrical Characteristics at Ta=25°C

#### Fig.1 Large Current R Load Switching Circuit

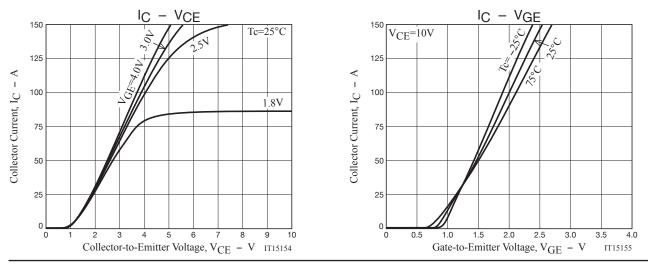


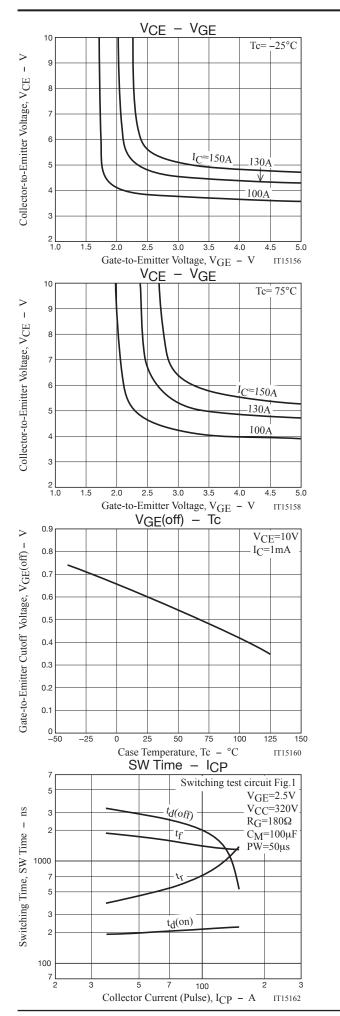
Note1. Gate Series Resistance  $R_G \ge 160\Omega$  is recommended for protection purpose at the time of turn OFF. However, if  $dv / dt \le 400V / \mu s$  is satisfied at customer's actual set evaluation,  $R_G < 160\Omega$  can also be used.

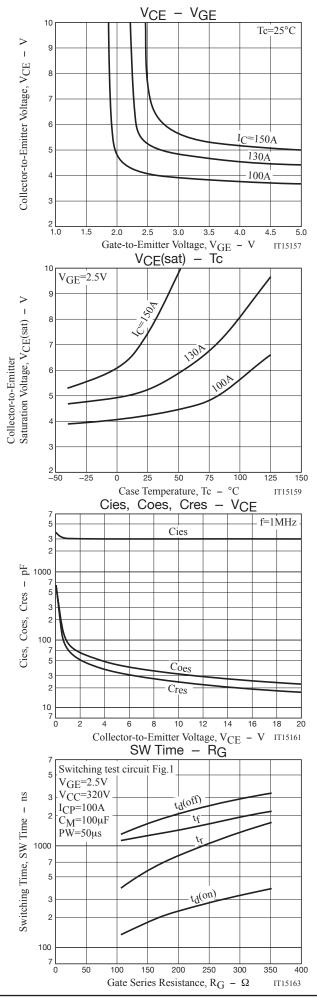
Note2. The collector voltage gradient dv / dt must be smaller than 400V / µs to protect the device when it is turned off.

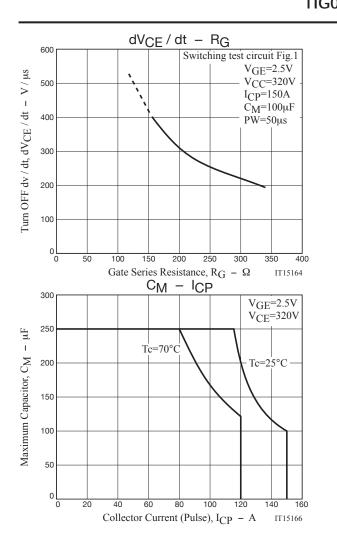
#### **Ordering Information**

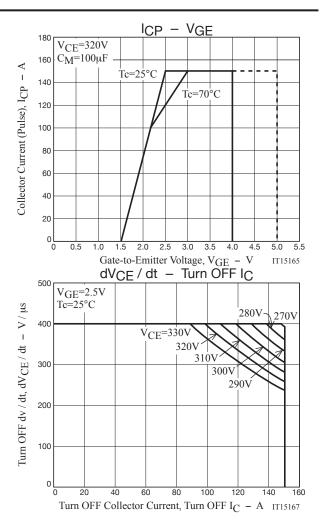
3				
Device Package		Shipping	memo	
TIG064E8-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free	











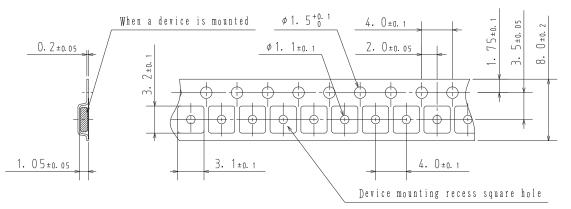
### Embossed Taping Specification TIG064E8-TL-H

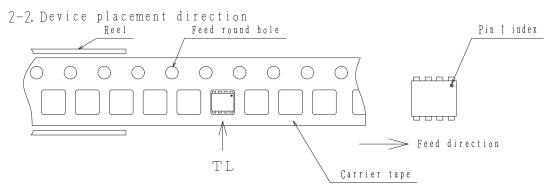
1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1) Outer BOX (A-7)
ECH8	СРН6	3,000	15,000	90,000	5 reels contained 6 inner boxes contained
_	_				Dimensions:mm (external) Dimensions:mm (external)
					183×72×185 440×195×210
Packing met	Type LOT	No. tity in	-> (11 -> (2) ->	nner box label Outer box label   nit:mm) It is a label at the time of factory shipments   The form of a label may change in physical distribution process.   59 108   000000 It is a construction process.   59 108   000000 It is a construction process.   59 It is a construction process.   000000 It is a construction preseconstruction	

2. Taping configuration

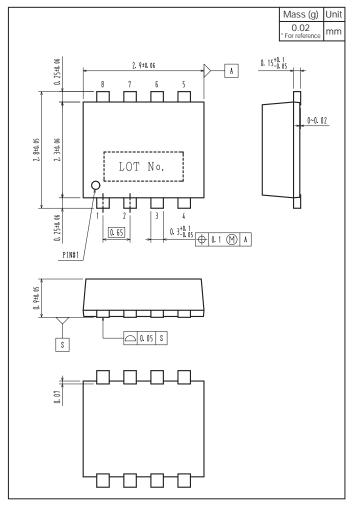
2-1. Carrier tape size (unit:mm)



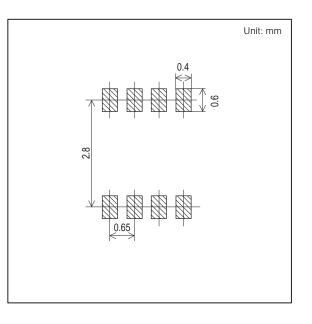


Those with pin 1 index on the feed hole side ·····TL

## Outline Drawing TIG064E8-TL-H



Land Pattern Example



Note : TIG064E8 has protection diode between gate and emitter but handling it requires sufficient care to be taken.

Any and all SANYO Semiconductor Co.,Ltd. products described or contained herein are, with regard to "standard application", intended for the use as general electronics equipment. The products mentioned herein shall not be intended for use for any "special application" (medical equipment whose purpose is to sustain life, aerospace instrument, nuclear control device, burning appliances, transportation machine, traffic signal system, safety equipment etc.) that shall require extremely high level of reliability and can directly threaten human lives in case of failure or malfunction of the product or may cause harm to human bodies, nor shall they grant any guarantee thereof. If you should intend to use our products for new introduction or other application different from current conditions on the usage of automotive device, communication device, office equipment, industrial equipment etc. , please consult with us about usage condition (temperature, operation time etc.) prior to the intended use. If there is no consultation or inquiry before the intended use, our customer shall be solely responsible for the use.

Specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

SANYO Semiconductor Co.,Ltd. assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein.

Regarding monolithic semiconductors, if you should intend to use this IC continuously under high temperature, high current, high voltage, or drastic temperature change, even if it is used within the range of absolute maximum ratings or operating conditions, there is a possibility of decrease reliability. Please contact us for a confirmation.

SANYO Semiconductor Co.,Ltd. strives to supply high-quality high-reliability products, however, any and all semiconductor products fail or malfunction with some probability. It is possible that these probabilistic failures or malfunction could give rise to accidents or events that could endanger human lives, trouble that could give rise to smoke or fire, or accidents that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

In the event that any or all SANYO Semiconductor Co.,Ltd. products described or contained herein are controlled under any of applicable local export control laws and regulations, such products may require the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written consent of SANYO Semiconductor Co.,Ltd.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the SANYO Semiconductor Co.,Ltd. product that you intend to use.

Upon using the technical information or products described herein, neither warranty nor license shall be granted with regard to intellectual property rights or any other rights of SANYO Semiconductor Co.,Ltd. or any third party. SANYO Semiconductor Co.,Ltd. shall not be liable for any claim or suits with regard to a third party's intellectual property rights which has resulted from the use of the technical information and products mentioned above.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.